

IN THE SPECIFICATION:

On page 1, immediately after the title, please insert the following paragraph and heading as follows:

This specification for the instant application should be granted the priority date of December 4, 2002, the filing date of the corresponding German patent application 102 56 696.8 as well as the priority date of 13 November 2003, the filing date of the corresponding International patent application PCT/EP2003/012892.

Background of the Invention.

On page 4, line 1, please insert the following heading:

--Summary of the Invention--

On page 8, line 11, please insert the following heading:

--Brief Description of the Drawings--

On page 9, line 6, please insert the following heading:

--Description of Specific Embodiments--.

On page 11, line 17 through page 12, line 2, please amend this paragraph as follows:

The MFC 24 has an outlet line 29 that leads into a gas-washing bottle 31, which is also designated as a bubbler. Liquid isopropyl alcohol (IPA) is contained in the bubbler 31, and the outlet line 29 of the MFC 24 extends into a region below the surface of the IPA liquid. The bubbler 31 furthermore has an outlet line 34 that leads to the inlet 16 of the hood 15. An inlet 35 of the outlet line 34 of the bubbler 31 is disposed above the IPA liquid 32.

On page 27, after line 8, please insert the following two new paragraphs:

--The specification incorporates by reference the disclosure of German priority document 102 56 696.8 filed December 4, 2002 and PCT/EP2003/012689 filed November 13, 2003.

The present invention is, of course, in no way restricted to the specific disclosure of the

specification and drawings, but also encompasses any modifications within the scope of the appended claims.—

In addition, please add the attached abstract to the specification:

Abstract of the Disclosure

A method of drying substrates, especially semiconductor wafers, after a wet treatment thereof in treatment liquid, including forming a gas mixture that comprises a carrier gas and an active substituent and that reduces the surface tension of the treatment liquid by conveying carrier gas through a liquid of the active substituent; actively controlling a concentration of the active substituent in the gas mixture and the temperature of the liquid of the active substituent to a predetermined temperature in an open or closed loop manner; applying the gas mixture to the treatment liquid; and moving the substrates out of the treatment liquid by generating a relative movement between the substrates and the treatment liquid.